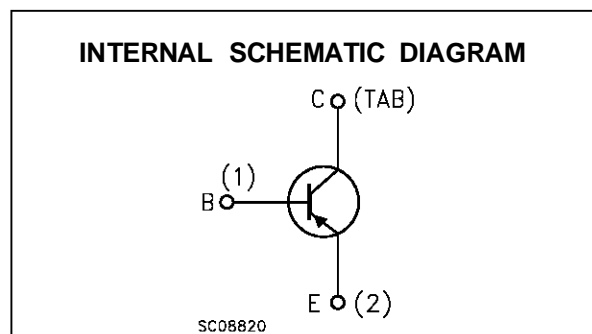
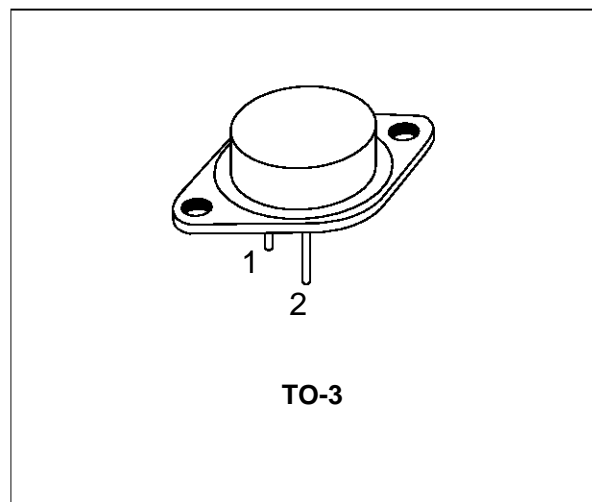


## SILICON PNPSWITCHING TRANSISTOR

■ SGS-THOMSON PREFERRED SALESTYPE

**DESCRIPTION**

The MJ2955 is a silicon epitaxial-base planar PNP transistors in TO-3 metal case, intended for power switching circuits, series and shunt regulators, output stages and hi-fi amplifiers.



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	- 100	V
$V_{CER}$	Collector-Emitter Voltage ( $R_{BE} \leq 100\Omega$ )	- 70	V
$V_{CEO}$	Collector-emitter Voltage ( $I_B = 0$ )	- 60	V
$V_{EBO}$	Emitter-base Voltage ( $I_C = 0$ )	- 7	V
$I_C$	Collector Current	- 15	A
$I_B$	Base Current	- 7	A
$P_{tot}$	Total Dissipation at $T_c \leq 25^\circ C$	150	W
$T_{stg}$	Storage Temperature	-65 to 200	$^\circ C$
$T_j$	Max. Operating Junction Temperature	200	$^\circ C$

**THERMAL DATA**

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.17	°C/W
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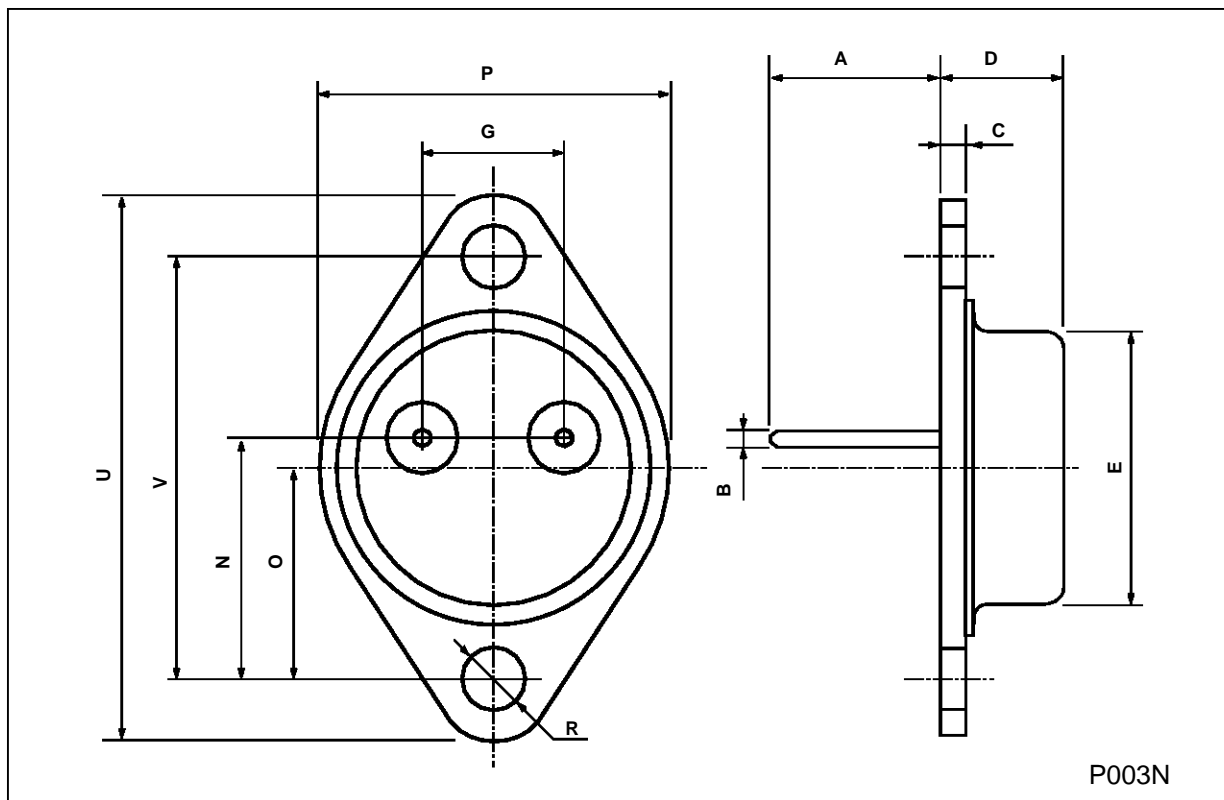
**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>C EX</sub>	Collector Cut-off Current (V <sub>BE</sub> = 1.5V)	V <sub>CB</sub> = -100 V V <sub>CB</sub> = -100 V      T <sub>case</sub> = 150 °C			- 1 - 5	mA mA
I <sub>C EO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = - 30 V			- 0.7	mA
I <sub>E BO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = - 7 V			- 5	mA
V <sub>C ER(sus)*</sub>	Collector-emitter Sustaining Voltage (R <sub>BE</sub> = 100 Ω)	I <sub>C</sub> = - 200 mA	- 70			V
V <sub>C EO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = - 200 mA	- 60			V
V <sub>C E(sat)*</sub>	Collector-emitter Saturation Voltage	I <sub>C</sub> = - 4 A      I <sub>B</sub> = - 0.4 A I <sub>C</sub> = - 10 A      I <sub>B</sub> = - 3.3 A			-1 -3	V V
V <sub>B E*</sub>	Base-emitter Voltage	I <sub>C</sub> = - 4 A      V <sub>CE</sub> = - 4 A			- 1.8	V
h <sub>F E*</sub>	DC Current Gain	I <sub>C</sub> = - 4 A      V <sub>CE</sub> = - 4 V I <sub>C</sub> = - 10 A      V <sub>CE</sub> = - 4 V	20 5		70	
f <sub>T</sub>	Transition-Frequency	I <sub>C</sub> = - 0.5 A      V <sub>CE</sub> = 5 V	4			MHz

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

**TO-3 (H) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		11.7			0.460	
B	0.96		1.10	0.037		0.043
C			1.70			0.066
D			8.7			0.342
E			20.0			0.787
G		10.9			0.429	
N		16.9			0.665	
P			26.2			1.031
R	3.88		4.09	0.152		0.161
U			39.50			1.555
V		30.10			1.185	



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